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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/840,125	05/06/2004	Steve Ming Ting	TSM03-0945	7245
43859 7590 04/06/2009 SLATER & MATSUI, L.L.P. 17950 PRESTON ROAD, SUITE 1000 DALLAS, TX 75252			EXAMINER NADAV, ORI	
			ART UNIT 2811	PAPER NUMBER
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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Response to Arguments

Applicant argues that the phrase "a notched spacer is thinner at a first portion closer to the surface of the substrate than at a second portion being further from the substrate" is synonymous with "a notched spacer is thinner along the surface of the substrate." Applicant further explains and provides reasons as to why there is support in the specification for the claimed limitations of a notched spacer being thinner near the substrate.

Applicant does not explain why the phrase "a notched spacer is thinner at a first portion closer to the surface of the substrate than at a second portion being further from the substrate" is synonymous with "a notched spacer is thinner along the surface of the substrate." Please note that the term "along" means "in a line matching the length or direction of". Therefore, the phrase "a notched spacer is thinner at a first portion closer to the surface of the substrate than at a second portion being further from the substrate" is not synonymous with the phrase "a notched spacer is thinner in a line matching the length or direction of the surface of the substrate."

Furthermore, as explained in previous office actions, there is no explicit teaching and adequate description in the disclosure and in the drawings, as originally filed, for the claimed limitation of a notched spacer is thinner in a line matching the length or direction of (along) the surface of the substrate.

Applicant argues that Kinugawa does not teach implanting the n regions in the substrate 11, because "as seen in Kinugawa Figure 3C; or that a p-well has a conductivity type N. Neither supposition is supported by Kinugawa. As seen from Figure 3C, the implant does not reach the n layer 11 and the implanted area 12 is p-type".

The implant does not have to reach the n layer in order for the implant to be located in substrate 11. The entire slab which includes well 12 and the implanted areas is considered to be the substrate, and thus all the doped regions are formed in the substrate 11.

The rest applicant's arguments were adequately addressed in previous office actions.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ori Nadav whose telephone number is 571-272-1660. The examiner can normally be reached between the hours of 7 AM to 4 PM (Eastern Standard Time) Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Lynne Gurley can be reached on 571-272-4670. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published

applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

O.N.
4/6/2009

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